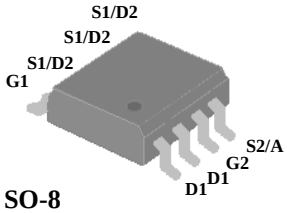
AP6901AGSM-HF

Halogen-Free Product

Advanced Power Electronics Corp.

DUAL N-CHANNEL MOSFET WITH SCHOTTKY DIODE

- ▼ **Simple Drive Requirement**
- ▼ **DC-DC Converter Suitable**
- ▼ **Fast Switching Performance**
- ▼ **RoHS Compliant & Halogen-Free**



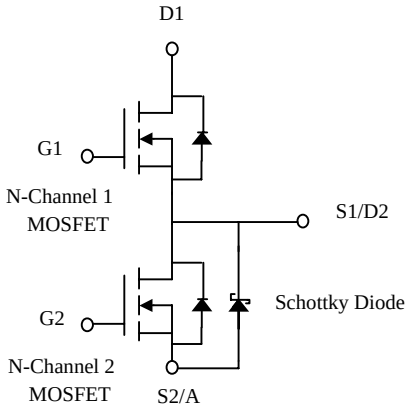
SO-8

CH-1	BV_{DSS}	30V
	$R_{DS(ON)}$	16.5mΩ
	I_D	7.4A
CH-2	BV_{DSS}	30V
	$R_{DS(ON)}$	16mΩ
	I_D	9.3A

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The SO-8 package is widely preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.



Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		Channel-1	Channel-2	
V_{DS}	Drain-Source Voltage	30	30	V
V_{GS}	Gate-Source Voltage	±20	±20	V
I_D@T_A=25℃	Continuous Drain Current[3]	7.4	9.3	A
I_D@T_A=70℃	Continuous Drain Current[3]	5.9	7.5	A
I_{DM}	Pulsed Drain Current[1]	30	30	A
P_D@T_A=25℃	Total Power Dissipation	1.4	2.2	W
T_{STG}	Storage Temperature Range	-55 to 150		℃
T_J	Operating Junction Temperature Range	-55 to 150		℃

Thermal Data

Symbol	Parameter	Value		Units
		Typ.	Max.	
Rthj-a (CH-1)	Thermal Resistance Junction-ambient[3]	70	90	℃/W
Rthj-a (CH-2)	Thermal Resistance Junction-ambient[3]	42	55	℃/W

CH-1 Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	30	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V, I_D=7A	-	12	16.5	mΩ
		V_{GS}=4.5V, I_D=5A	-	18	26	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	1	1.65	3	V
g_{fs}	Forward Transconductance	V_{DS}=10V, I_D=5A	-	15	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V, V_{GS}=0V	-	-	10	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Q_g	Total Gate Charge	I_D=5A	-	9.5	15.2	nC
Q_{gs}	Gate-Source Charge	V_{DS}=15V	-	3	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=4.5V	-	4	-	nC
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=15V	-	10	-	ns
t_r	Rise Time	I_D=1A	-	6	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3.3Ω	-	22	-	ns
t_f	Fall Time	V_{GS}=10V	-	4	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	1140	1820	pF
C_{oss}	Output Capacitance	V_{DS}=15V	-	120	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	95	-	pF
R_g	Gate Resistance	f=1.0MHz	-	1.3	2.6	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=1.2A, V_{GS}=0V	-	-	1.2	V
t_{rr}	Reverse Recovery Time	I_S=5A, V_{GS}=0V	-	18	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	10	-	nC

CH-2 Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	30	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V, I_D=9A	-	12	16	mΩ
		V_{GS}=4.5V, I_D=6A	-	18	26	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	1	1.65	3	V
g_{fs}	Forward Transconductance	V_{DS}=10V, I_D=6A	-	16	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V, V_{GS}=0V	-	-	100	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Q_g	Total Gate Charge	I_D=6A	-	9.5	15.2	nC
Q_{gs}	Gate-Source Charge	V_{DS}=15V	-	3	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=4.5V	-	4	-	nC
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=15V	-	9	-	ns
t_r	Rise Time	I_D=1A	-	5	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3.3Ω	-	22	-	ns
t_f	Fall Time	V_{GS}=10V	-	5	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	1180	1888	pF
C_{oss}	Output Capacitance	V_{DS}=15V	-	165	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	105	-	pF
R_g	Gate Resistance	f=1.0MHz	-	1.3	2.6	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=1.8A, V_{GS}=0V	-	-	1.2	V
t_{rr}	Reverse Recovery Time	Is=6A, V_{GS}=0V,	-	17	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	8	-	nC

Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

3.Surface mounted on 1 in^2 copper pad of FR4 board, t ≤10 sec.

Schottky Specifications@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_F	Forward Voltage Drop	I_F=1.0A	-	0.47	0.5	V
I_{rm}	Maximum Reverse Leakage Current	V_r=24V	-	0.004	0.2	mA
	Maximum Reverse Leakage Current	V_r=24V,T_j=75℃	-	0.5	1	mA

Channel-1

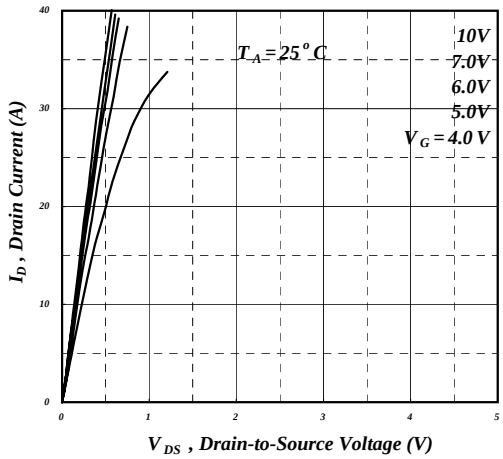


Fig 1. Typical Output Characteristics

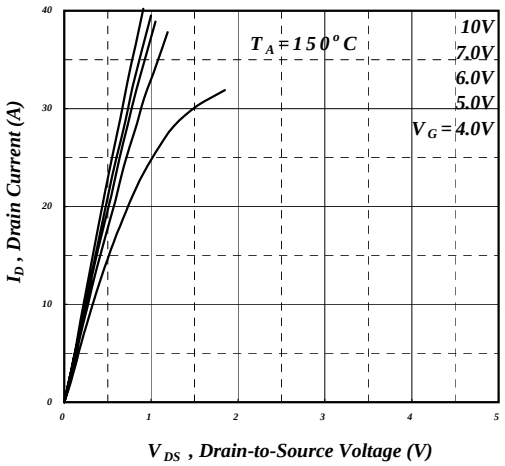


Fig 2. Typical Output Characteristics

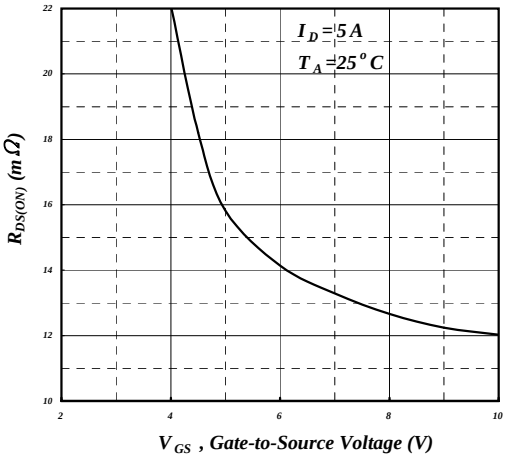


Fig 3. On-Resistance v.s. Gate Voltage

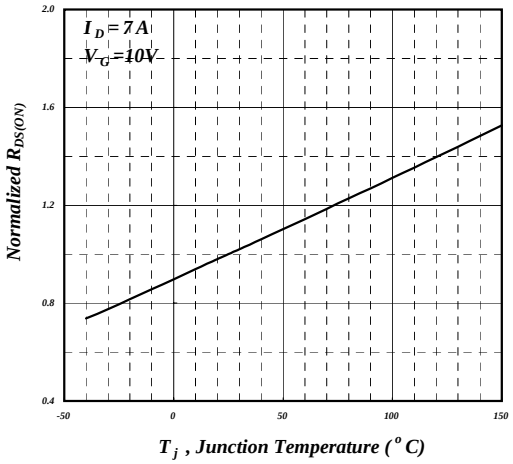


Fig 4. Normalized On-Resistance v.s. Junction Temperature

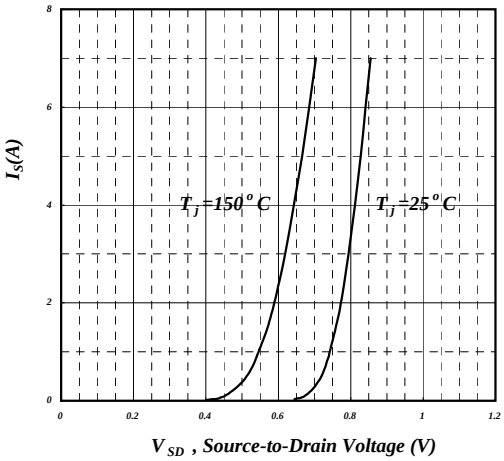


Fig 5. Forward Characteristic of Reverse Diode

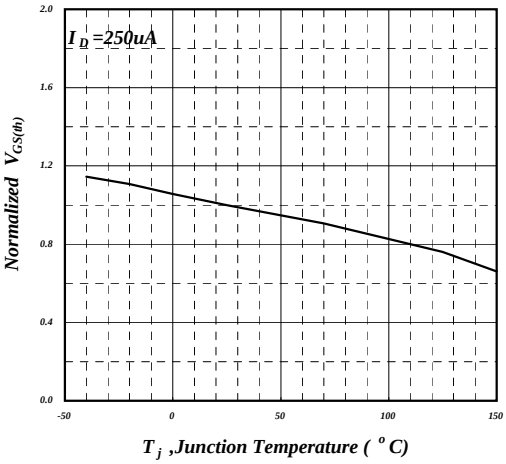


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

Channel-1

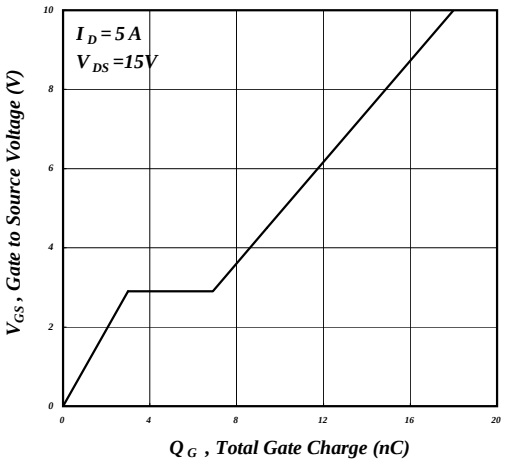


Fig 7. Gate Charge Characteristics

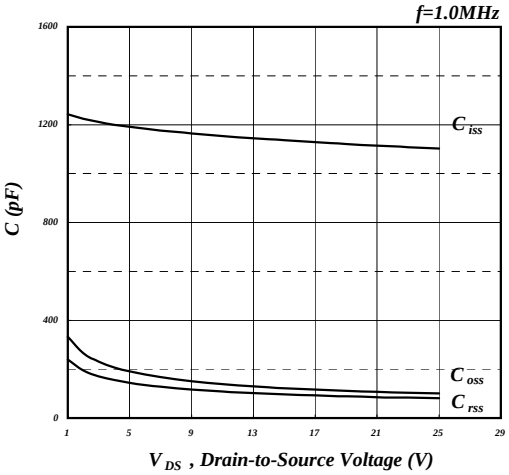


Fig 8. Typical Capacitance Characteristics

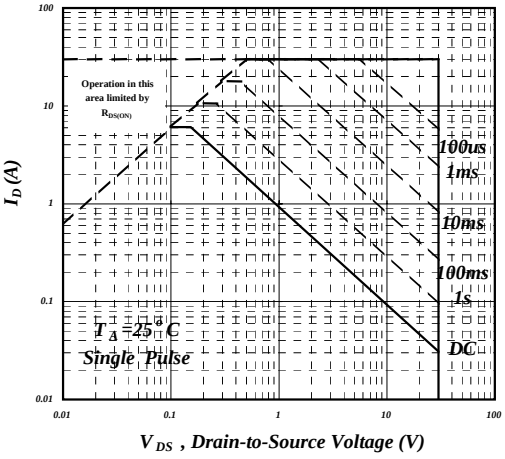


Fig 9. Maximum Safe Operating Area

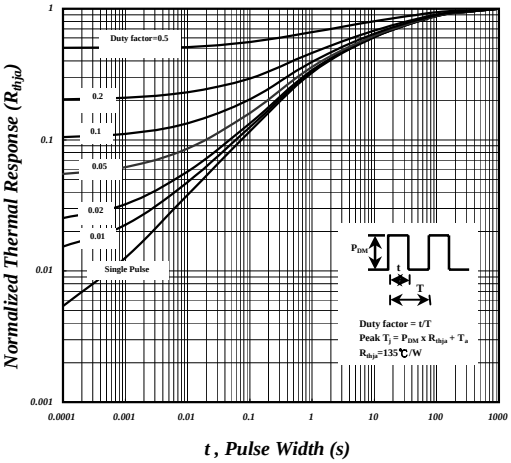


Fig 10. Effective Transient Thermal Impedance

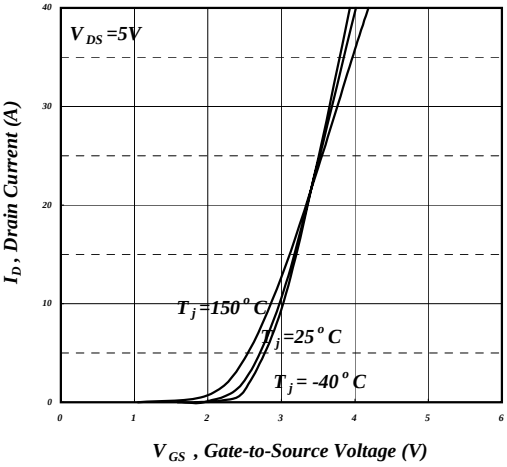


Fig 11. Switching Time Waveform

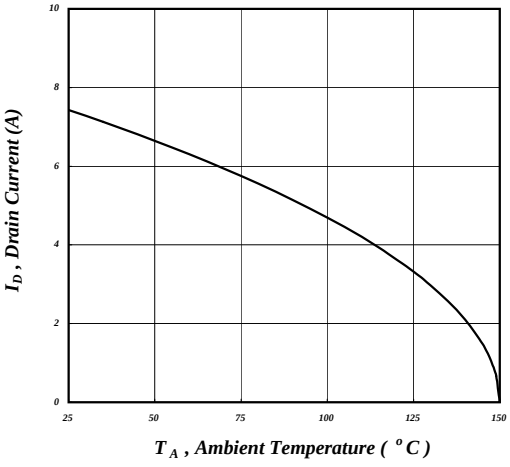


Fig 12. Maximum Continuous Drain Current v.s. Ambient Temperature

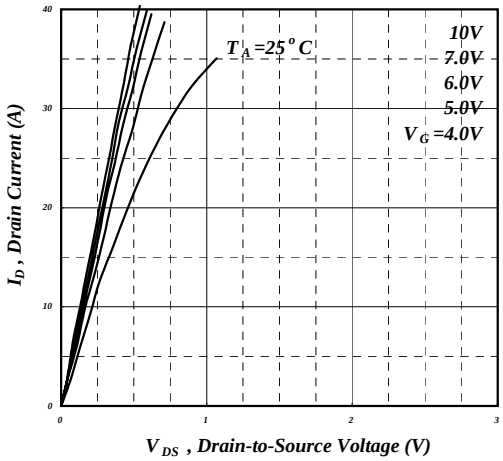


Fig 1. Typical Output Characteristics

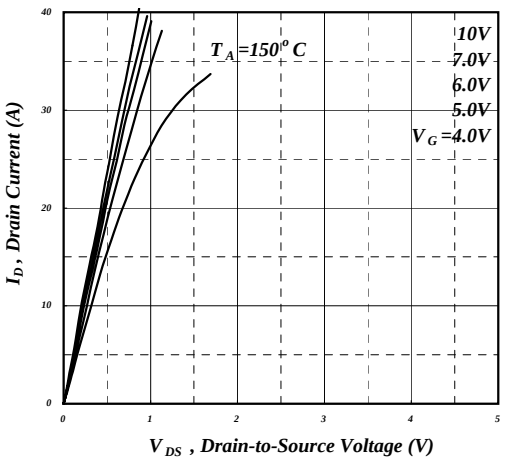


Fig 2. Typical Output Characteristics

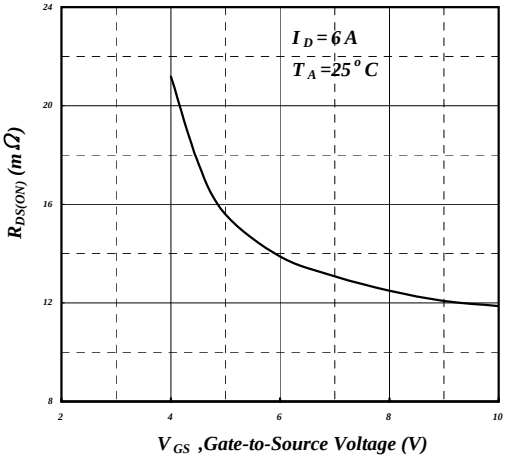


Fig 3. On-Resistance v.s. Gate Voltage

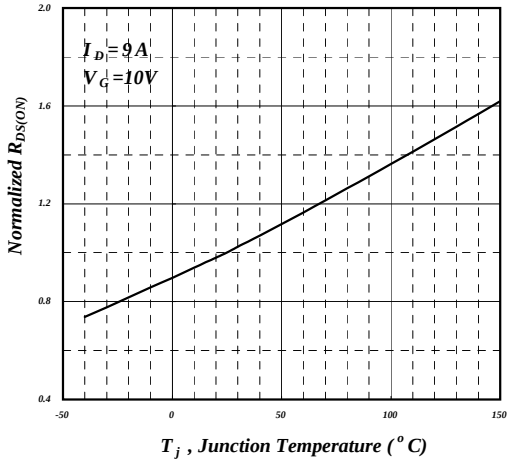


Fig 4. Normalized On-Resistance v.s. Junction Temperature

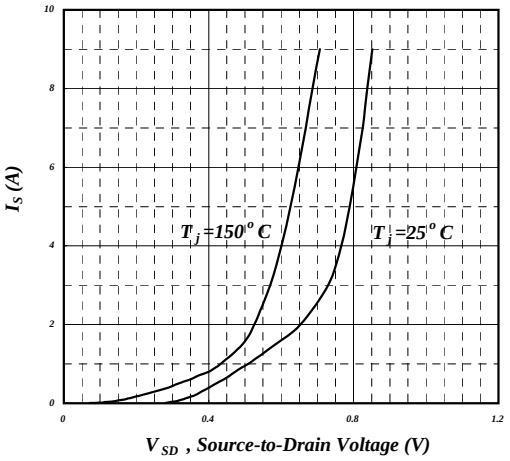


Fig 5. Forward Characteristic of Reverse Diode

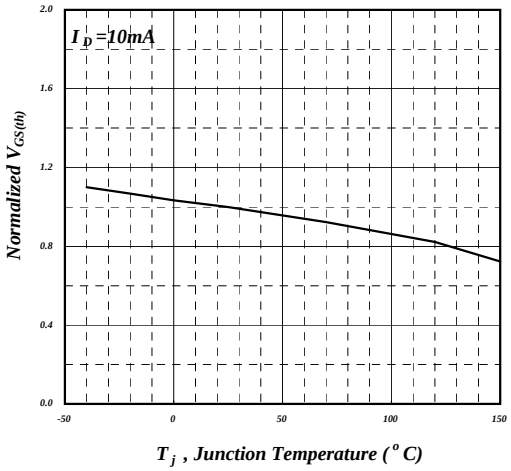


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

Channel-2

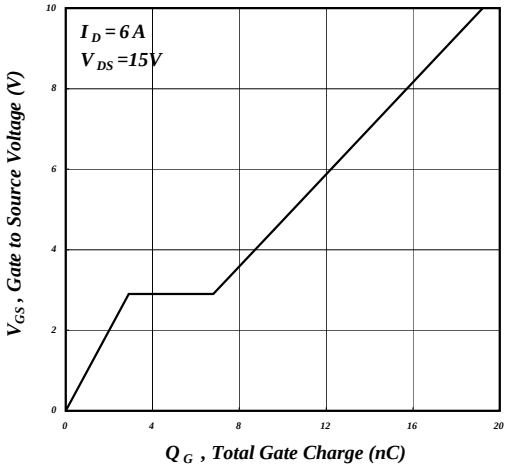


Fig 7. Gate Charge Characteristics

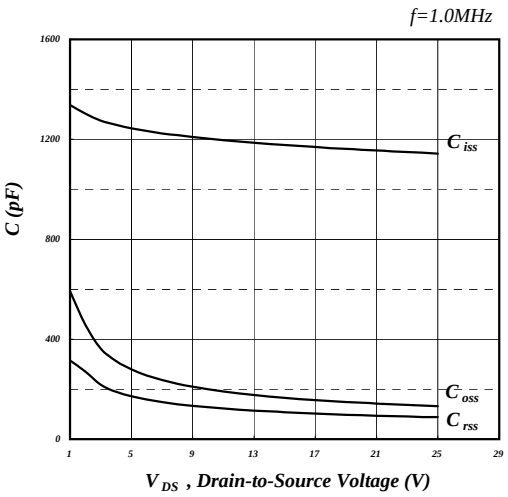


Fig 8. Typical Capacitance Characteristics

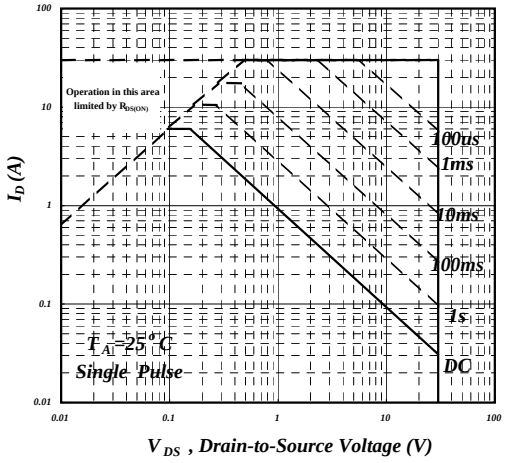


Fig 9. Maximum Safe Operating Area

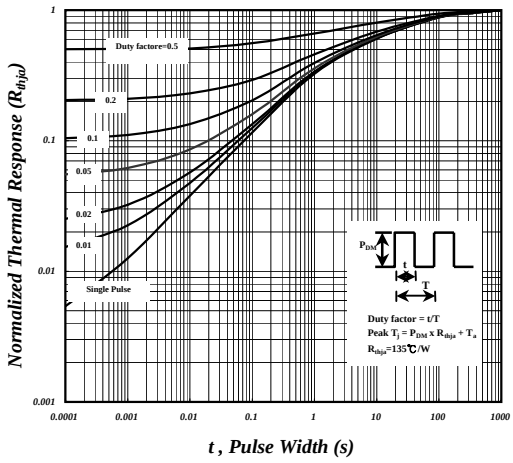


Fig 10. Effective Transient Thermal Impedance

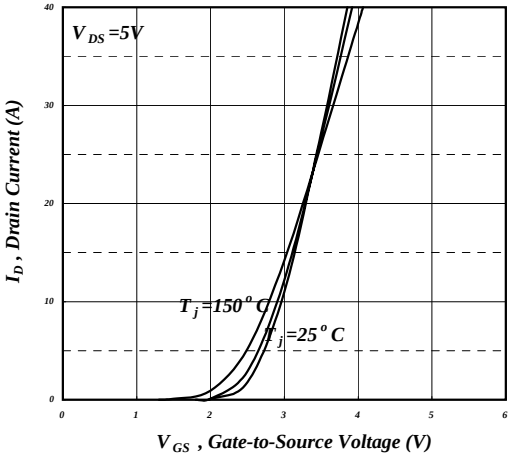


Fig 11. Transfer Characteristics

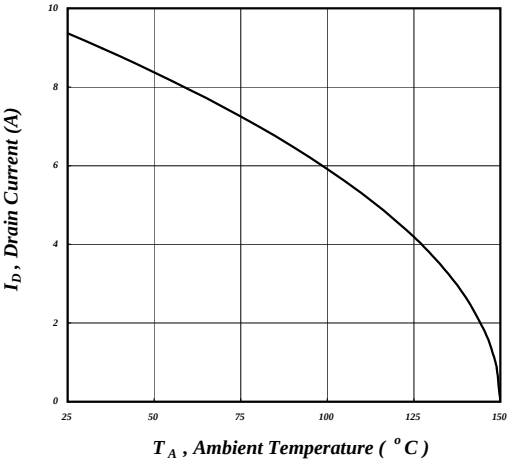


Fig 12. Maximum Continuous Drain Current v.s. Ambient Temperature

Schottky

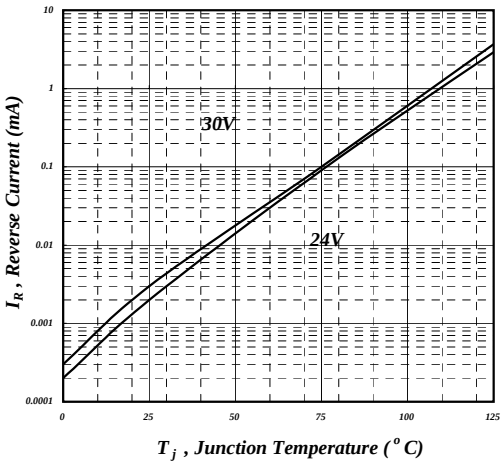


Fig 1. Reverse Current vs Junction Temperature

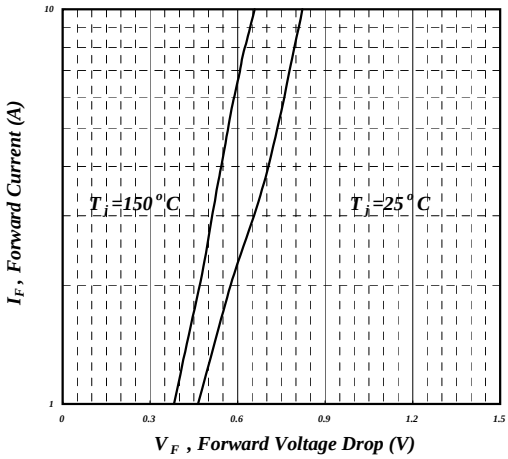


Fig 2. Typical Forward Characteristics